



# *900 MHz DIGITAL*

Single line ADPCM  
cordless phone with CIDCW  
Model: VT1910C

## **THEORY OF OPERATION**

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## Section 1 RF Section Overview

### 1.0 Introduction

The basic function of the base and handset RF sections is to provide a full duplex wireless link between the handset and base sections of the telephone. This is accomplished by setting up two simultaneous communications links between the handset and base RF boards. The RF receiver and transmitter circuitry essentially provide a link between the microphone and speaker in the handset to the telephone line in the base set. In this way the phone performs exactly as a corded phone, except without the cord.

The frequency at which the handset transmits to the base is centered around 926.55 MHz, and the frequency at which the base transmits to the handset is centered around 903.8 MHz. Unlike a normal 46/49 MHz cordless phone, which directly modulates audio (voice) onto the RF carrier, a phone using the Mark III module first digitizes the audio signal and then modulates high speed data onto the RF carrier. The data rate which is modulated onto the RF carrier is 48 kbps. On the receiver side, the data is extracted and then converted back into the original audio signal.

It is important to note that the synthesizer / prescaler IC only operates up to 500 MHz. The VCO's therefore oscillate at roughly 450 MHz. The 900 MHz signals needed for the transmit and receive sections are generated from the second harmonic of the VCO frequencies.

The following section will outline the transmit frequencies used as well as the corresponding LO frequency which is used for the receiver. This is followed by the Block diagram and a block by block functional description of the modules.

## 1.1 Frequency Tables

This section outlines the RF frequencies and corresponding channel numbers. The handset uses a high side LO while the base uses a low side LO to down-convert the incoming signal.

### 1.1.1 Handset

Channel	Transmit	Receive	RX LO
1	925.05	902.3	913.0
2	925.35	902.6	913.3
3	925.65	902.9	913.6
4	925.95	903.2	913.9
5	926.25	903.5	914.2
6	926.55	903.8	914.5
7	926.85	904.1	914.8
8	927.15	904.4	915.1
9	927.45	904.7	915.4
10	927.75	905.0	915.7

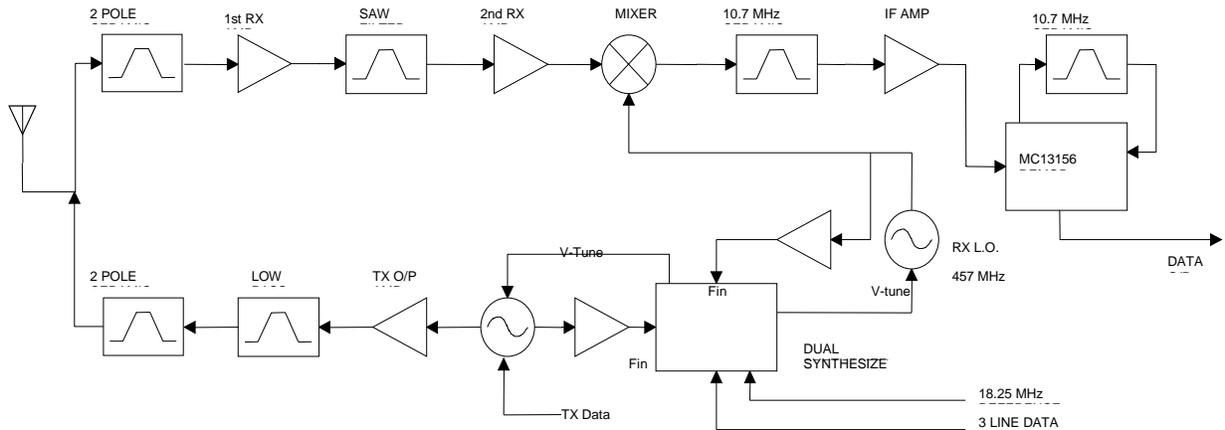
### 1.1.1 Base

Channel	Transmit	Receive	RX LO
1	902.3	925.05	914.35
2	902.6	925.35	914.65
3	902.9	925.65	914.95
4	903.2	925.95	915.25
5	903.5	926.25	915.55
6	903.8	926.55	915.85
7	904.1	926.85	916.15
8	904.4	927.15	916.45
9	904.7	927.45	916.75
10	905.0	927.75	917.05

## 1.2

**Block Diagram**

Both the handset and base RF sections follow the same block diagram shown below with only minor changes to incorporate the different transmit and receive frequencies.



**Figure 1. RF Section Block Diagram**

As can be seen by the block diagram, there are several important input/output signals which are necessary for operation of the RF section (this does not include the separate supply lines for both TX and RX sections). An 18.25 MHz reference is present for use in the frequency synthesizers. The accuracy of this 18.25 MHz input will affect the transmit and receive frequencies. In order to ensure proper operation of the RF sections, the 18.25 MHz reference signal must be at least 500 mV in amplitude. Also present is the 3-line serial data bus on which data is transferred to the synthesizers to set both the transmit and receive frequencies.

The modulation input allows digital data to be modulated directly onto the TX carrier. The Data output is the demodulated signal after being filtered and shaped by a comparator. The data is then sent to the AMD ASIC where the original voice signal is reconstructed.

The RF section performs a single down-conversion of the incoming RF signal to 10.7 MHz where it is demodulated and sent to the AMD ASIC. The transmit section directly modulates the carrier.

The following section explains the individual blocks in the RF section in detail. All reference to part numbers correspond to the handset schematic.

## Section 2 RF Section Detailed Operation

### 2.1 Antenna Section

#### 2.1.1 Antenna

The antenna is a device which allows effective conversion of energy from air to the RF circuitry. The antennas used are a retractable 1/2 wave with 2.5 dB gain relative to an isotropic radiator and a fixed 1/4 wave antenna with roughly 0 dB gain relative to an isotropic radiator. The duplexer and filters which follow the antenna, require a 50 ohm match to operate properly. The antenna is not matched to 50 ohms and requires a simple microstrip matching network to achieve this. If a network analyzer is attached to the BFA connector after disconnecting the duplexer, the antenna match may be measured. In order to achieve a good 50 ohm match, one must be careful not to obstruct the antenna as any object near the antenna will affect its impedance.

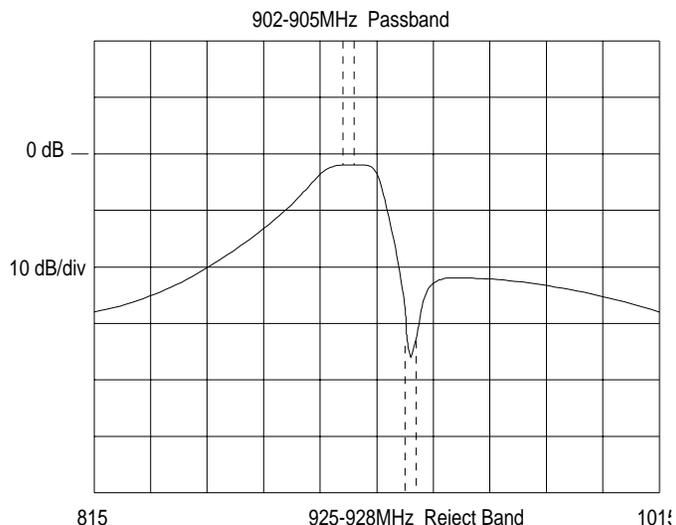
#### 2.1.2 Duplexer

The Duplexer ensures that the two bandpass filters do not interact with each other. It accomplishes this by making each filter see a high impedance from the opposite filter in its own passband. This is necessary to ensure that both filters work effectively when connected together. If the Duplexer were not present, mismatches from one filter would cause the passband of the other to be distorted and this would degrade performance.

The Duplexer itself is simply composed of two microstrip and discrete filters which shift each filters out of band match to a high impedance. To ensure that the Duplexer is operating correctly, the match looking into the filters from the BFA connector may be measured. To do this it is necessary to remove the 0 ohm resistor which connects the antenna to the Duplexer. A return loss of approximately 15 dB should be measured for both the TX and RX bands.

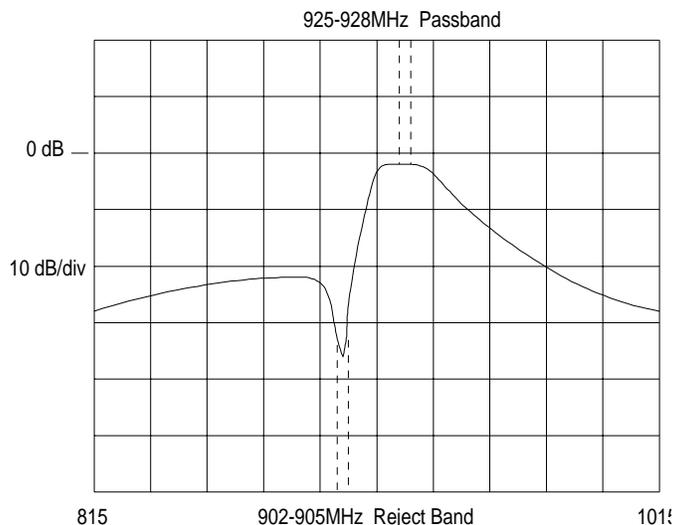
#### 2.1.3 RX, TX Bandpass Filters

The RX and TX bandpass filters provide two functions. The first is to effectively pass the correct frequencies to the RX and TX sections. It is important especially for the RX section that these filters have a low insertion loss in order to ensure a low front end noise figure. These filters are also designed to provide > 25 dB rejection for the opposite band. This means that the transmit carrier will be attenuated by at least 25 dB before entering the receive section of the phone. A plot of the low band filter is shown below.



**Figure 2 Low band Ceramic filter response**

For this filter the insertion loss is less than 3dB at 902 to 905MHz while the 925-928MHz band has >25dB attenuation. This filter is used for the RX filter in the handset or the TX filter in the base. The high band filter characteristic is shown below. This filter is used for the handset TX filter and base RX filter.



**Figure 3 High band ceramic filter response**

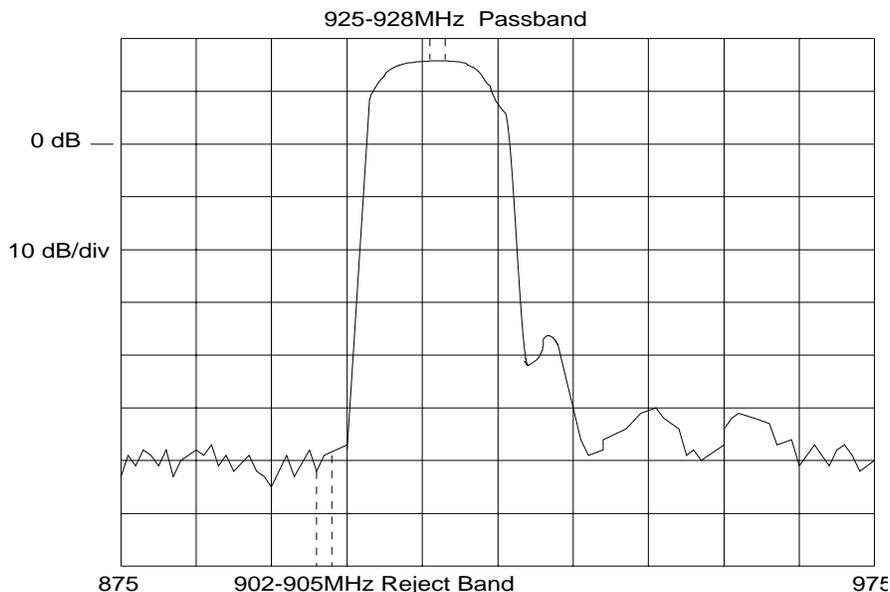
## 2.2 Receive Section

### 2.2.1 RX Amps and SAW Filter

The purpose of the first RX amp is to provide enough gain that the noise figure of the RX section is fixed to as low a value as possible. It must provide a good  $50 \Omega$  match to both the RX bandpass filter and the SAW filter. This amplifier must also have good power handling capability due to the limited filtering which precedes it. The design employs a collector inductor to improve the output power capability of the transistor. This form of matching also ensures that the gain of this stage is not too wide band further improving its performance by allowing it to effectively reject signals which are far out of its passband.

Directly following the first RX amp is the SAW filter. This filter is responsible for the bulk of the filtering in the receive section. It provides more than 40dB of image rejection and TX carrier suppression. The insertion loss of this filter is relatively high due to its SAW implementation. It has an insertion loss of less than 5 dB, typically 4 dB. An amplifier is required before this SAW filter to keep the noise figure low. If it were not present, the noise figure of the phone would increase by the 4 dB loss associated with the SAW filter.

The second RX amp provides a limited amount of gain. Its main function is to ensure that the mixer sees a good wideband match. Measuring the RX gain from the BFA connector to the output of this amplifier will produce results as shown in Figure 4 below.



**Figure 4. RX Front end Response**

### 2.2.2 RX Mixer

The function of the mixer is to combine the incoming signal with a LO signal in order to convert the desired signal to the 10.7 MHz IF frequency. The mixer used for this task is a dual gate FET (CF739R). The LO and RF signals are placed on the gates of the FET and the IF signal is coupled off of the drain. The FET provides conversion gain along with adequate power handling characteristics. Both the RF and LO ports are shorted to ground by rectangular microstrip inductors. These inductors provide a high impedance at both the RF and LO frequencies while presenting a very low impedance at the IF frequency. The mixer is followed by an emitter follower which converts the high impedance output of the mixer to a 330 ohm output suitable for directly driving the IF ceramic filters. The gain for the pair (mixer and follower) is about 8 dB (50 ohms in, 330 ohms out).

### 2.2.3 RX VCO and LO Buffer

The RX VCO is a Colpitt's type oscillator operating at about 450 MHz with a frequency selective network tuned to about 900 MHz on the collector. The frequency of oscillation is controlled by a varactor diode in the tank circuit connected to the base of the transistor. This diode is connected to the loop voltage from the RX synthesizer. Rough tuning is achieved with a variable chip cap. This capacitor is used to center the tuning voltage to ensure reliable operation over a wide temperature range and also to compensate for variances in component values.

The 450 MHz LO for the PLL is coupled off of the emitter of the VCO transistor. This is lightly coupled to ensure that the VCO is not loaded by the PLL. The LO Buffer isolates the PLL from the VCO preventing the TX VCO from interfering with the RX VCO and vice versa. The 900 MHz RX LO signal for the Mixer is coupled off the collector of the VCO transistor.

### 2.2.4 RX Synthesizer

The PLL and prescaler for both the TX and RX sides are now combined into one IC. The Synthesizer receives channel information from the embedded microprocessor in the AMD ASIC via the serial buss. It also requires a stable 18.25 MHz reference which is also supplied from the AMD ASIC.

A passive loop filter is employed to connect the synthesizer to the VCO. This tuning voltage may be observed from test point Z1 on the bottom side of the PCB. The loop filter cutoff frequency is set to about 1 kHz to allow relatively fast power-up times.

**2.2.5 IF Amplifier Stage**

There is only one stage of discrete IF amplification. Transistor Q5 is used as an amplifier with 330 ohms input and output impedance. The rest of the IF gain is provided by the FM demod IC discussed below.

**2.2.6 IF Filtering**

The choice of 10.7 MHz as an IF frequency, allows the use of relatively inexpensive filters. Two ceramic filters are used to achieve the desired adjacent channel suppression. Two different bandwidth filters are used, 230 kHz and 150 kHz, so that any shifting in the passband does not narrow the bandwidth excessively.

**2.2.7 Demodulator, Data comparator, Mute Comparator**

This RF section uses a MC13156 FSK demodulator. It incorporates all three of the above functions into a single IC.

The Quadrature voltage may be observed from test point [TBD]. This voltage should nominally be 1.2 V when a signal is center tuned.

The data stream which comes out of the demodulator has a peak to peak amplitude of approx. 0.5V. In order to be of use it is first filtered and converted to a digital (0 to 5V) signal by using a comparator inside the IC.

## 2.3 Transmit Section

### 2.3.1 TX Amp

There is one transistor which provide the necessary gain for the transmit section. Transistor [TBD] amplifies the signal from the TX VCO. The output power is set to the required -5 dBm (this is the power level at the BFA connector required to guarantee less then 50mV/meter radiated field strength measured at 3 meters).

### 2.3.2 TX VCO

The basic operation of the TX VCO is the same as the RX VCO, except for one detail. The TX VCO is also FSK modulated by the transmit data through a second varactor in the tank (25kHz peak to peak). The data is first filtered and then the amplitude is adjusted through [TBD] to set the deviation of the data modulation.

### 2.3.3 TX Synthesizer/PLL

The TX PLL is combined into one IC with the RX PLL. See above. The loop filter cutoff frequency is about 100 Hz. This allows the data modulation to include frequencies down to about 100 Hz. The power-up time of the TX PLL is not critical.

## Section 3 Baseband Section

### 3.0 General Description

The AMD ASIC is a custom designed IC based on the core platform of the AMD CT2 baseband chipset. This custom modification contracted by VTech removes the protocol blocks associated with the CT2 TDD architecture and replaces it with a VTech proprietary FDD protocol block.

The AMD ASIC performs virtually all the non-RF functions with the exception of the line interface block on the base unit and the LCD driver function on the handset. The base and handset ASIC's are identical with the exception of the ROM code which will be masked into the ASIC prior to mass production.

### 3.1 Detailed Functional Description

The principle components are:

#### 3.1.1 Protocol Functions

The protocol block conducts a signaling and a voice channel in the transmit and receive directions. All data I/O are CMOS levels.

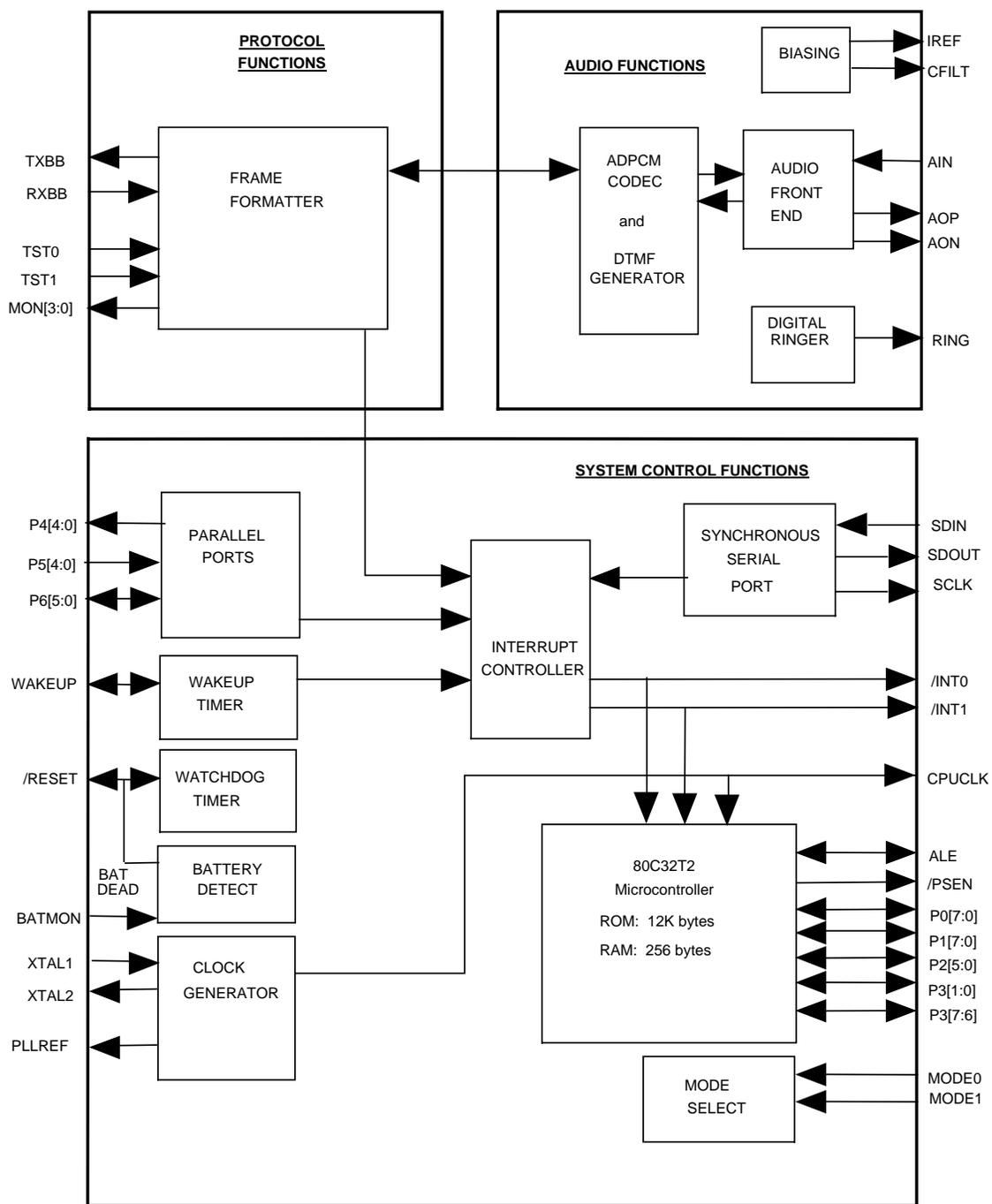
#### 3.1.2 Audio Functions

- 1) CODEC. The CODEC transcodes analog voice signals and 32 kbps ADPCM data.
- 2) Audio Front End. The audio front end connects the analog voice I/O pins to the CODEC.
- 3) Tone Ringer. The tone ringer produces digital square-wave ringing tone signals for output on the RING pin.
- 4) Biasing. The biasing circuits establish precision currents and voltage references to support audio and battery detection analog operations.
- 5) DTMF Generator. The DTMF generator produces digitally-generated tones for DTMF dialing and call progress tones.

#### 3.1.3 System Control Functions

- 1) Microcontroller. An 8-bit 80C32T2 microcontroller executes the program and controls the protocol logic and other hardware configuration. It includes 12 Kbytes of mask-programmable ROM and 256 bytes of RAM. It also includes an asynchronous serial port.
- 2) Synchronous Serial Port. The serial port provides a synchronous serial link to devices such as RF synthesizers, serial EEPROMs, etc.

- 3) Peripheral Ports. The peripheral ports are for general purpose I/O functions. One port is designed such that any change of state generates an interrupt for the key scanning function.
- 4) Battery Level Detector. The battery level detector reports the low battery condition to prevent misoperation when batteries are low. It also emits a dead battery control signal which can be used to hold the device in a disabled, low power state and a high level detection for battery charging control.
- 5) Watchdog Timer. The watchdog timer protects the system from errant software by periodically issuing a reset unless serviced by software.
- 6) Wakeup Timer. The wakeup timer is a multivibrator controlled by external passive components to effect a low power periodic wakeup for call detection.
- 7) Interrupt Controller. The interrupt controller structures the various interrupts for manageable service by the microcontroller.
- 8) Clock Generator. The clock generator creates required internal timing signals from the crystal operating at 18.25 MHz. It also generates a PLL reference at the crystal frequency.
- 9) Address decoder. The address decoder generates strobes accessing selected address spaces in the device.



**Figure 5. AMD ASIC - Internal Structure Diagram**

## Section 4 Complete System Description

### 4.0 General Description for Handset

#### 4.0.1 RF / ASIC Interface

Basically the interface between the RF section for both base and handset and the AMD ASIC is the same. There is the serial buss connection to control the synthesizers, and there are separate controls for powering the transmit and receive sections of the radio.

#### 4.0.2 Handset Serial Buss Connections

Also connected on the serial buss is an EEPROM used to store CID information and the handset security code. In addition, an LCD driver is also tied onto the same serial buss and is used to control the LCD display functions on the handset

#### 4.0.3 Other Handset Connections

The handset microphone, receiver and alerter (ringer) are connected directly to the AMD ASIC. General I/O is used for keyboard scanning as well as to control other miscellaneous functions such as LCD and keypad backlighting.

### 4.1 General Description for Base

#### 4.1.1 RF / ASIC Interface

Basically the interface between the RF section for both base and handset and the AMD ASIC is the same. There is the serial buss connection to control the synthesizers, and there are separate controls for powering the transmit and receive sections of the radio.

#### 4.1.2 Base Serial Buss Connections

Also connected on the serial buss is an EEPROM used to store the base security code as well as all the user programmed speed dial numbers.

#### 4.1.3 Other Base Connections

The line interface section is discrete and is external to the AMD ASIC. After the line interface section and hybrid, the transmit and receive audio path are routed to the corresponding audio connections on the AMD ASIC. A discrete Caller ID signal decoder IC is connected in the line interface and the decoded data is routed to the AMD ASIC.

General I/O is used for keyboard scanning as well as to control other miscellaneous functions such as LED illumination.